Power Supply of Front-End Electronic in RICH/TORCH Upgrade

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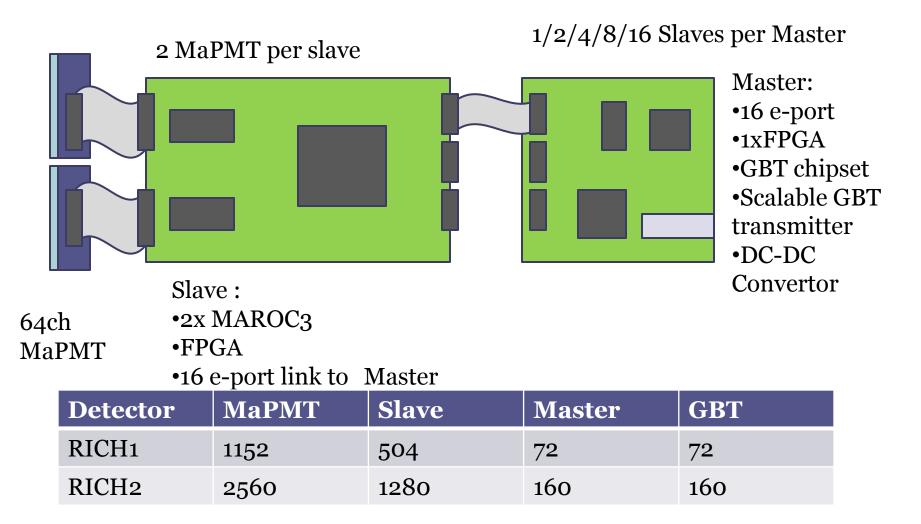




RICH/TORCH Upgrade FE Electronics

- New devices: Hamamasu R7600/R11265 MaPMT, in RICH, and MCP in TORCH,
- Binary readout / TOF measurement,
- Higher readout rate, un-triggered readout,
- Use of GBT chipset,
- Use of DC-DC convertor.
- Cabling would be very similar to current RICH,
- Would re-use the current power supply module for RICH upgrade, same power supply for TORCH.

RICH Front End



Devices and Assumptions

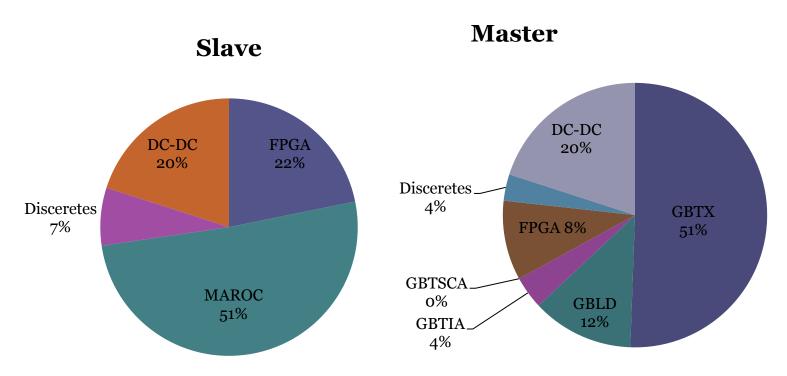
- Hamamatsu R7600/R11265 64ch MaPMT,
- The MAROC3 64-ch, <u>250mW</u>,
- Rad-hard or tolerant FPGA, <u>300mW</u>,
- Discretes, <u>100mW</u> per board,
- GBT user bandwidth 2.5~3.2Gbps, GBTX-<u>1.5W</u>, GBLD – <u>380mW</u>, GBTIA-<u>123mW</u>, GBTSCA – unknown.
- Scalable GBT interface, primary GBT has both trans. and recv., add-on GBT has trans. only.
- Assumption Ave. Occupancy 1% !

RICH Voltages and Currents

Voltage	Device	Est. Current (mA) Slave/Master
1.2V	FPGA (core), e-port drive & receiver	100 / 100
1.5V	GBTX	None / 1100
2.5v	FPGA I/O, GBTIA, GBLD, GBTSCA, Flash RAM, MAROC3	400 / 300
3.3v	"Legacy" device s, FPGA I/O	20 / 20

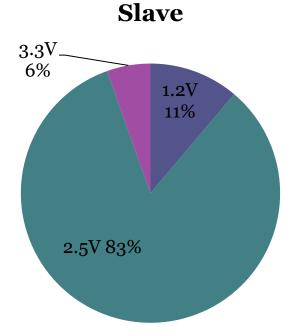
- Hopefully never need 3.3v,
- The Actel rad-hard *ProASIC3E* use 1.5v core voltage, no need for 1.2v,
- Radiation not so bad comments?

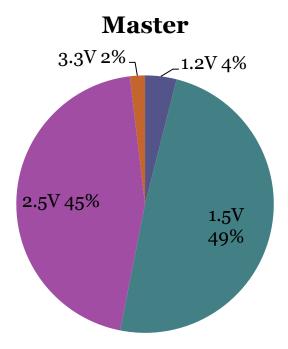
RICH Power Consumption by Device



• Slave – 1379mW, Master 3084mW

RICH Power Consumption by Voltage

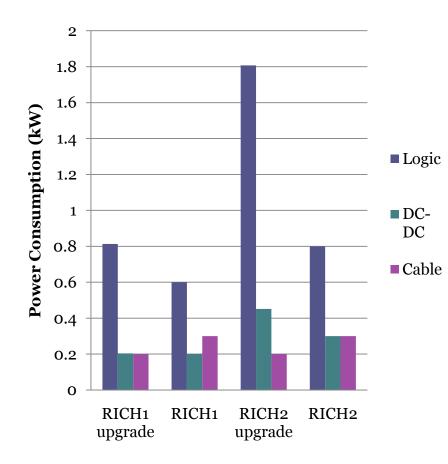




• Logic power only.

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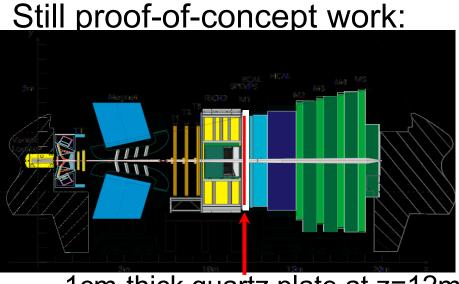
RICH Summary



- 16MaPMT

 (1024ch)/GBT, need
 simulation results,
- RICH1 1kW,
- RICH2 2.2kW
- 4 Supply voltages, minimum 2.

TORCH Current baseline design



1cm-thick quartz plate at z=12m

7.44m Beampipe hole Quartz block

slide)

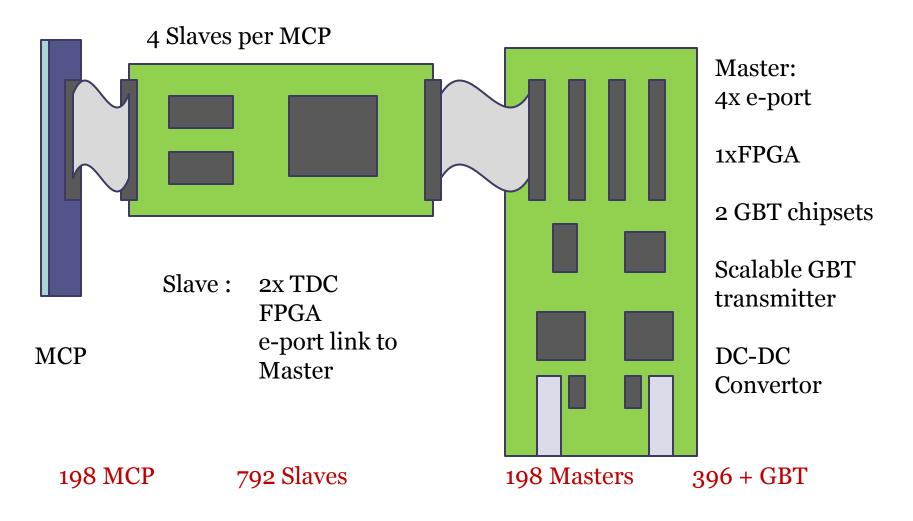
Rectangular quartz block:

7.44m wide in x (124 photodetectors each side)

- 6.12m high in y (102 photodetectors each side)
- ... for a total of 452 photodetectors

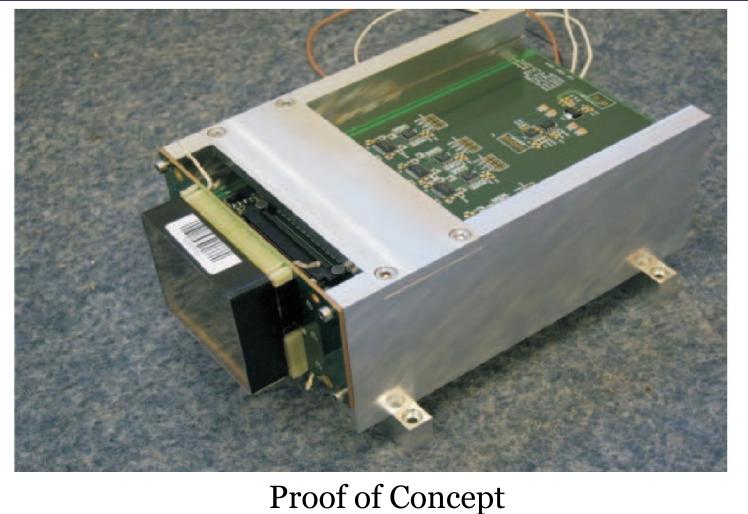
Square hole for beampipe in the center (26cm x 26cm) with mirrored edges Mirrored surfaces have reflectivity 0.9

TORCH Front End



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TORCH Front End



Devices and Assumptions

- Burle-Photonis XP85022 or customised 128x8ch MCP,
- The "Perfect TDC" 128-ch with analogue input stage (amplifier and discriminator), 6ps, <u>2W</u>,
- Rad-hard or tolerant FPGA, <u>300mW</u>,
- Discretes, <u>200mW</u> per board,
- GBT user bandwidth 3.2Gbps, GBTX-<u>1.5W</u>, GBLD <u>380mW</u>, GBTIA-<u>123mW</u>, GBTSCA <u>unknow</u>.
- Scalable GBT interface, primary GBT has both trans. and recv., add-on GBT has trans. only.
- Assumption Ave. Occupancy 0.5% !

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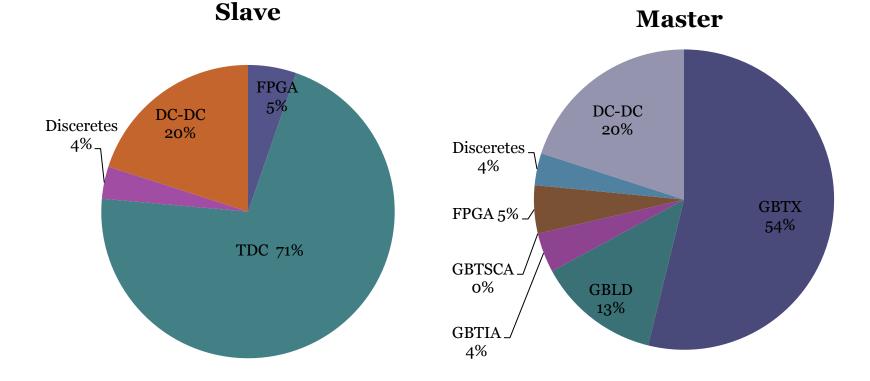
TORCH - Voltage and Current

Voltage	Device	Est. Current (mA) Slave/Master
1.2V	FPGA (core), e-port drive & receiver	100 / 100
1.5V	GBTX x 2	None / 2100
2.5V	FPGA I/O, GBTIA, GBLD, GBTSCA, Flash RAM, TDC	1750/ 550
3.3v	"Legacy" device s, FPGA I/O	20 / 20

- Hopefully never need 3.3v,
- TDC may need "clean" analogue 2.5v,
- The Actel rad-hard *ProASIC3E* use 1.5v core voltage.

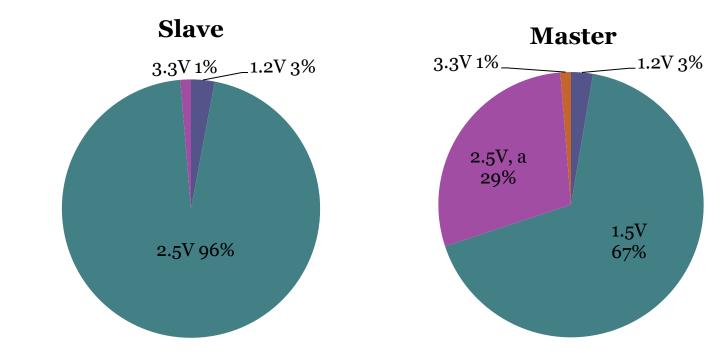
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Power Consumption - by Device



• Slave – 5641mW, Master – 5794mW

Power Consumption - by Voltage

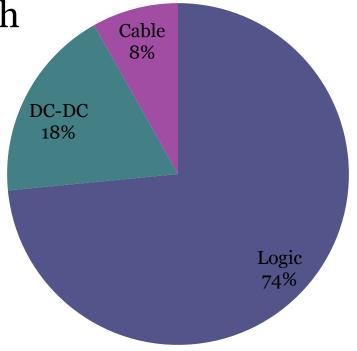


• Logic power only

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Summary - TORCH

- 198 MCP FE assembly, each gives 30W, 6.1kW in total
- 400 GBT,
- 4 Supply voltages, min 2.
- Simulation needed,
- According to Mat's simulation result: 9GBT/MCP, 50W/ MCP, 1800 GBTs, 10kW.



Thanks!

Backup Slides

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Commercial Rad Hard DC-DC Module

- An example: VPT-0510S
 - ^o 3.5-7v input 0.8-3.4 output, 33w max
 - 84-94% efficiency
 - 100krads